

R1LP5256E Series

256Kb Advanced LPSRAM (32k word x 8bit)

R10DS0070EJ0100 Rev.1.00 2011.04.13

Description

The R1LP5256E Series is a family of low voltage 256-Kbit static RAMs organized as 32,768-word by 8-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies. The R1LP5256E Series has realized higher density, higher performance and low power consumption. The R1LP5256E Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives. It has been packaged in 28-pin SOP and 28-pin TSOP.

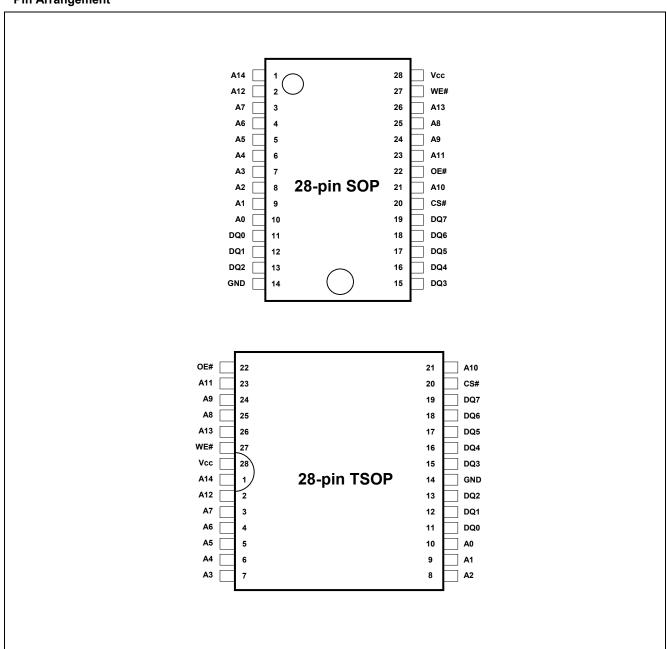
Features

- Single 4.5V~5.5V power supply
- Small stand-by current: 1µA (5.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

Ordering Information

Orderable Part Name	Access time	Temperature Range	Package	Shipping Container	Quantity	
R1LP5256ESP-5SR#B0	55 ns	0 ~ +70°C				
R1LP5256ESP-5SI#B0	22 118	-40 ~ +85°C		Tube	Max. 30pcs/Tube	
R1LP5256ESP-7SR#B0	70 ns	0 ~ +70°C	450-mil 28-pin	rube	Max. 300pcs/Inner Bag Max. 1200pcs/Inner Box	
R1LP5256ESP-7SI#B0	70 118	-40 ~ +85°C	plastic SOP		·	
R1LP5256ESP-5SR#S0	55 ns	0 ~ +70°C	PRSP0028DB-B			
R1LP5256ESP-5SI#S0	55 118	-40 ~ +85°C	(28P2W-C)	Embossed	1000pcs/Reel	
R1LP5256ESP-7SR#S0	70 ns	0 ~ +70°C		tape	1000pcs/Reel	
R1LP5256ESP-7SI#S0	70115	-40 ~ +85°C				
R1LP5256ESA-5SR#B0	55 ns	0 ~ +70°C				
R1LP5256ESA-5SI#B0	55 118	-40 ~ +85°C		Trav	Max. 234pcs/Tray	
R1LP5256ESA-7SR#B0	70 ns	0 ~ +70°C	8mm×13.4mm 28-pin plastic TSOP	Tray	Max. 1872pcs/Inner Box	
R1LP5256ESA-7SI#B0	70115	-40 ~ +85°C	(normal-bend type)			
R1LP5256ESA-5SR#S0	55 ns	0 ~ +70°C	DT0400074.4			
R1LP5256ESA-5SI#S0	00 118	-40 ~ +85°C	PTSA0028ZA-A (28P2C-A)	Embossed	1000pcs/Reel	
R1LP5256ESA-7SR#S0	70 ns	0 ~ +70°C	(==: 20 7.)	tape	1000pcs/Reel	
R1LP5256ESA-7SI#S0	10115	-40 ~ +85°C				

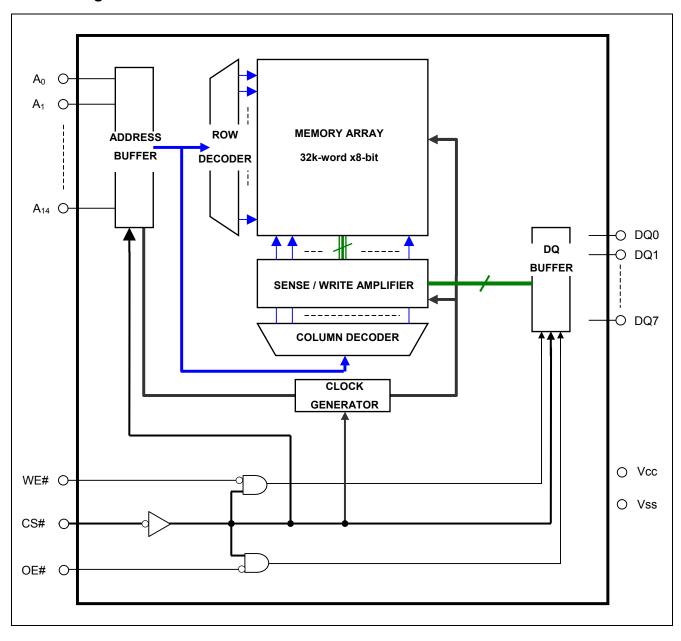
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A14	Address input
DQ0 to DQ7	Data input/output
CS#	Chip select
WE#	Write enable
OE#	Output enable

Block Diagram



Operation Table

CS#	WE#	OE#	DQ0~7	Operation
Н	Х	Х	High-Z	Stand-by
L	L	Х	Din	Write
L	Н	L	Dout	Read
L	Н	Н	High-Z	Output disable

Note 1. H: V_{IH} L:V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum

Parameter	Symbol	Symbol Value		unit	
Power supply voltage relative to Vss	Vcc	-0.3	-0.3 to +7		
Terminal voltage on any pin relative to Vss	V_{T}	-0.3 ^{*1} to Vcc+0.3 ^{*2}		V	
Power dissipation	P_T	0	0.7		
Operation temperature	Topr*3	R Ver.	0 to +70	• °C	
Operation temperature	ТОРІ	I Ver.	-40 to +85		
Storage temperature range	Tstg	-65 to	-65 to 150		
Storage temperature range under him	Tbias*3	R Ver.	0 to +70	°C	
Storage temperature range under bias	ามเสร	I Ver.	-40 to +85		

Note 1. –3.0V for pulse ≤ 30ns (full width at half maximum)

- 2. Maximum voltage is +7V.
- 3. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Operating Conditions

Parameter		Symbol	Min.	Тур.	Max.	Unit	Note
Supply voltage		Vcc	4.5	5.0	5.5	V	
		Vss	0	0	0	V	
Input high voltage		V _{IH}	2.2	-	Vcc+0.3	V	
Input low voltage		V_{IL}	-0.3	-	0.8	V	1
Ambient temperature range	R Ver.	Та	0	-	+70	°C	2
Ambient temperature range	I Ver.	Id	-40	-	+85	°C	2

Note 1. -3.0V for pulse ≤ 30 ns (full width at half maximum)

DC Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions			
Input leakage current	I _{LI}	-	-	1	μΑ	Vin = Vss to Vcc			
Output leakage current	I _{LO}	-	-	1	μА	CS# =V _{IH} C	or OE# =V _{IH} , to Vcc		
Average operating current	I _{CC1}	-	25	35	mA	-	duty =100%, II/O = 0mA Others = V _{IH} /V _{IL}		
	I _{CC2}	-	2	4	mA	CS# ≤ 0.2\	s, duty =100%, II/O = 0mA /, 0.2V, V _{IL} ≤ 0.2V		
Standby current	I _{SB}	-	-	3	mA	CS# =V _{IH} , Others = V			
Standby current		-	1 ^{*1}	2	μА	~+25°C	Vin = Vss to Vcc		
	-	-	-	3	μΑ	~+40°C	CS#≥ Vcc-0.2V		
	I _{SB1}	-	-	8	μΑ	~+70°C			
		-	-	10	μА	~+85°C			
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -1mA			
	V_{OH2}	Vcc - 0.5	-	-	V	I _{OH} = -0.1m	nA		
Output low voltage	V_{OL}	-	-	0.4	V	I _{OL} = 2mA			

Note 1. Typical parameter indicates the value for the center of distribution at 5.0V (Ta= 25°C), and not 100% tested.

^{2.} Ambient temperature range depends on R/I-version. Please see table on page 1.

Capacitance

$$(Vcc = 4.5V \sim 5.5V, f = 1MHz, Ta = 0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*2})$$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	6	pF	Vin =0V	1
Input / output capacitance	C _{I/O}	-	-	8	pF	VI/O =0V	1

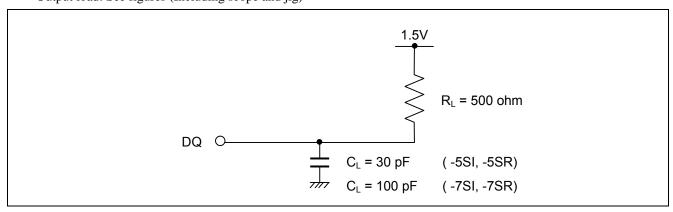
Note 1. This parameter is sampled and not 100% tested.

2. Ambient temperature range depends on R/I-version. Please see table on page 1.

AC Characteristics

Test Conditions (Vcc = $4.5V \sim 5.5V$, Ta = $0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*1}$)

- Input pulse levels: VIL = 0.6V, VIH = 2.4V
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.5V
- Output load: See figures (Including scope and jig)



Note 1. Ambient temperature range depends on R/I-version. Please see table on page 1.

Read Cycle

_		R1LP5256E**-5S*		R1LP525	6E**-7S*		
Parameter	Symbol	Min.	Max.	Min.	Max.	Unit	Note
Read cycle time	t _{RC}	55	-	70	-	ns	
Address access time	t _{AA}	-	55	-	70	ns	
Chip select access time	t _{ACS}	-	55	-	70	ns	
Output enable to output valid	toE	-	30	-	35	ns	
Output hold from address change	t _{OH}	10	-	10	-	ns	
Chip select to output in low-Z	t _{CLZ}	5	-	5	-	ns	2,3
Output enable to output in low-Z	t _{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t _{CHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1,2,3

Write Cycle

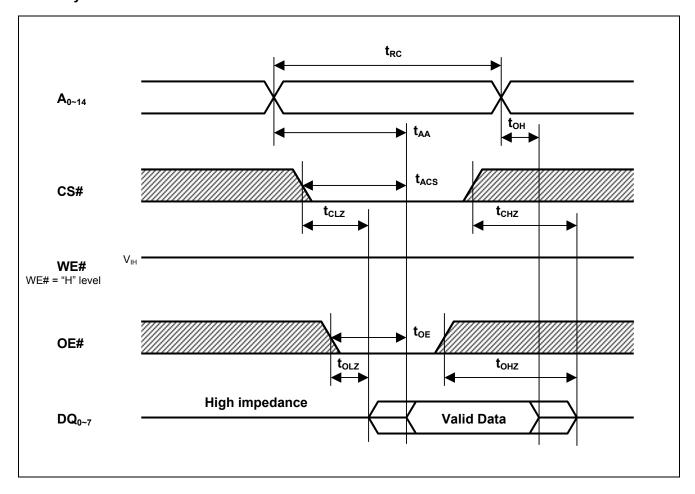
Parameter	Symbol	R1LP5256E**-5S*		R1LP525	56E**-7S*	Unit	Note
Faranietei	Syllibol	Min.	Max.	Min.	Max.	Offic	Note
Write cycle time	twc	55	-	70	-	ns	
Address valid to end of write	t _{AW}	50	-	65	-	ns	
Chip select to end of write	t _{CW}	50	-	65	-	ns	5
Write pulse width	t _{WP}	40	-	50	-	ns	4
Address setup time	t _{AS}	0	-	0	-	ns	6
Write recovery time	t _{WR}	0	-	0	-	ns	7
Data to write time overlap	t _{DW}	25	-	30	-	ns	
Data hold from write time	t _{DH}	0	-	0	-	ns	
Output enable from end of write	tow	5	-	5	-	ns	2
Output disable to output in high-Z t _{OHZ}		0	20	0	25	ns	1,2
Write to output in high-Z		0	20	0	25	ns	1,2

Note

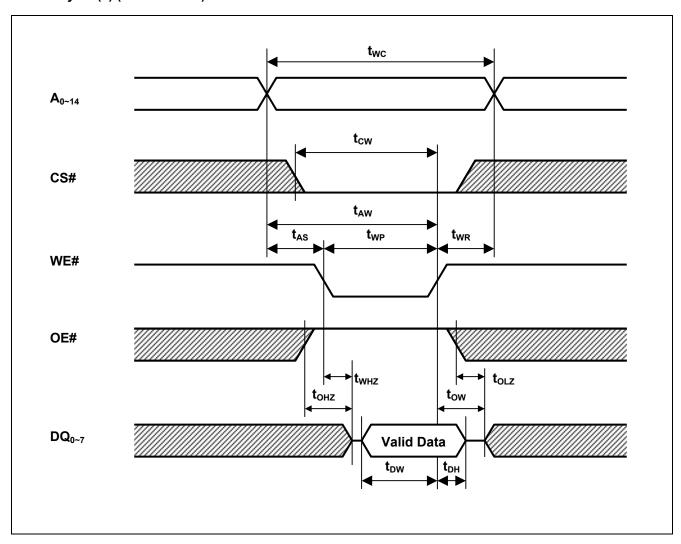
- 1. t_{CHZ}, t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
- 2. This parameter is sampled and not 100% tested.
- 3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
- 4. A write occurs during the overlap of a low CS#, a low WE#.
 - A write begins at the latest transition among CS# going low and WE# going low.
 - A write ends at the earliest transition among CS# going high and WE# going high.
 - t_{WP} is measured from the beginning of write to the end of write.
- 5. t_{CW} is measured from the later of CS# going low to end of write.
- 6. t_{AS} is measured the address valid to the beginning of write.
- 7. t_{WR} is measured from the earliest of CS# or WE# going high to the end of write cycle.
- 8. Don't apply inverted phase signal externally when DQ pin is output mode.

Timing Waveforms

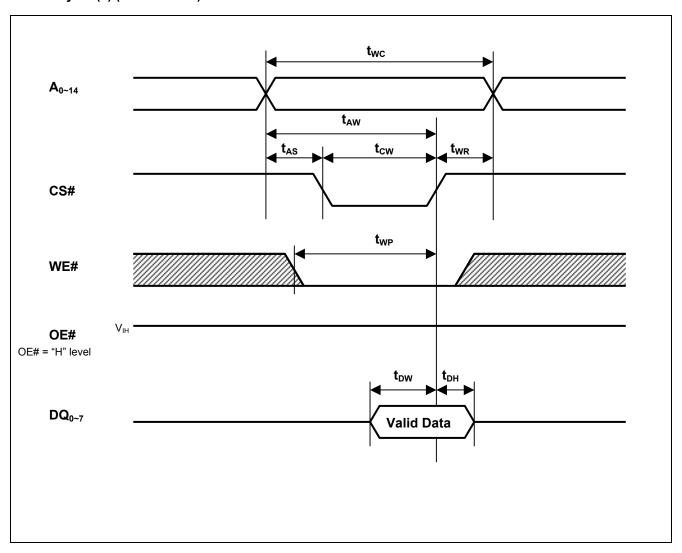
Read Cycle



Write Cycle (1) (WE# CLOCK)



Write Cycle (2) (CS# CLOCK)



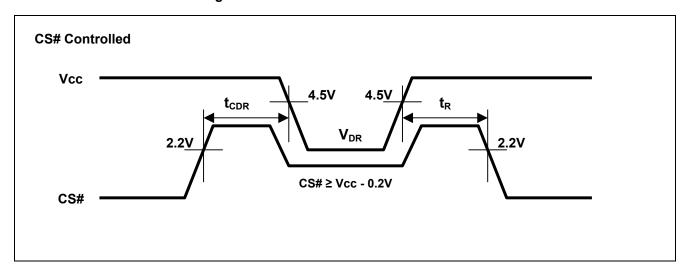
Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit		Test conditions*2
V _{CC} for data retention	V_{DR}	2.0	ı	5.5	>	Vin ≥ 0V CS# ≥ Vcc	c-0.2V
Data retention current	Iccdr	-	1 ^{*1}	2	μΑ	~+25°C	
		-	-	3	μΑ	~+40°C	Vcc=3.0V, Vin ≥ 0V, CS# ≥ Vcc-0.2V
		-	-	8	μΑ	~+70°C	C5# 2 VCC-0.2V
		-	-	10	μΑ	~+85°C	
Chip deselect to data retention time	t _{CDR}	0	-	-	ns	Soo roton	tion waveform
Operation recovery time	t _R	5	-	-	ms	See retention waveform.	

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25°C), and not 100% tested.

^{2.} CS# controls address buffer, WE# buffer, OE# buffer and Din buffer. If CS# controls data retention mode, Vin levels (address, WE#, OE#, DQ) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms



Revision History R1LP5256E Series Data Sheet
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			Description				
Rev.	Date	Page	Summary				
1.00	2011.04.13	-	First Edition issued				

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